

TCS1200

1200 Watts, 53 Volts Pulsed Avionics at 1030 MHz

PRELIMINARY SPECIFICATION

GENERAL DESCRIPTION

The TCS1200 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems at 1030 MHz, with the pulse width and duty required for TCAS applications. The device has gold thin-film metalization and emitter ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55TU-1

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

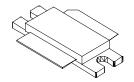
Device Dissipation @ 25°C¹ 2095 W

Maximum Voltage and Current

Collector to Base Voltage (BV $_{ces}$) 65 V Emitter to Base Voltage (BV $_{ebo}$) 3.5 V Collector Current (I $_c$) 60 A

Maximum Temperatures

Storage Temperature -65 to +200 °C Operating Junction Temperature +200 °C



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	Pulse Width = 32µs	1200			W
P_{g}	Power Gain	Duty Factor = 2%	10.2			dB
η_c	Collector Efficiency	$F = 1030 \text{ MHz}, V_{cc} = 53 \text{ Volts}$	45			%
R_{L}	Return Loss	Pin = 115 Watts	-10			dB
Tr	Rise Time				100	ns
Pd	Pulse Droop				0.7	dB
VSWR	Load Mismatch Tolerance ¹		3.0:1			

FUNCTIONAL CHARACTERISTICS @ 25°C

$\mathrm{BV}_{\mathrm{ebo}}$	Emitter to Base Breakdown	Ie = 40 mA	3.5		V
$\mathrm{BV}_{\mathrm{ces}}$	Collector to Emitter Breakdown	Ic = 100 mA	65		V
\mathbf{h}_{FE}	DC – Current Gain	Vce = 5V, $Ic = 5A$	20		
θjc^1	Thermal Resistance			0.02	°C/W

NOTES: 1. At rated output power and pulse conditions

Preliminary - May 2007

